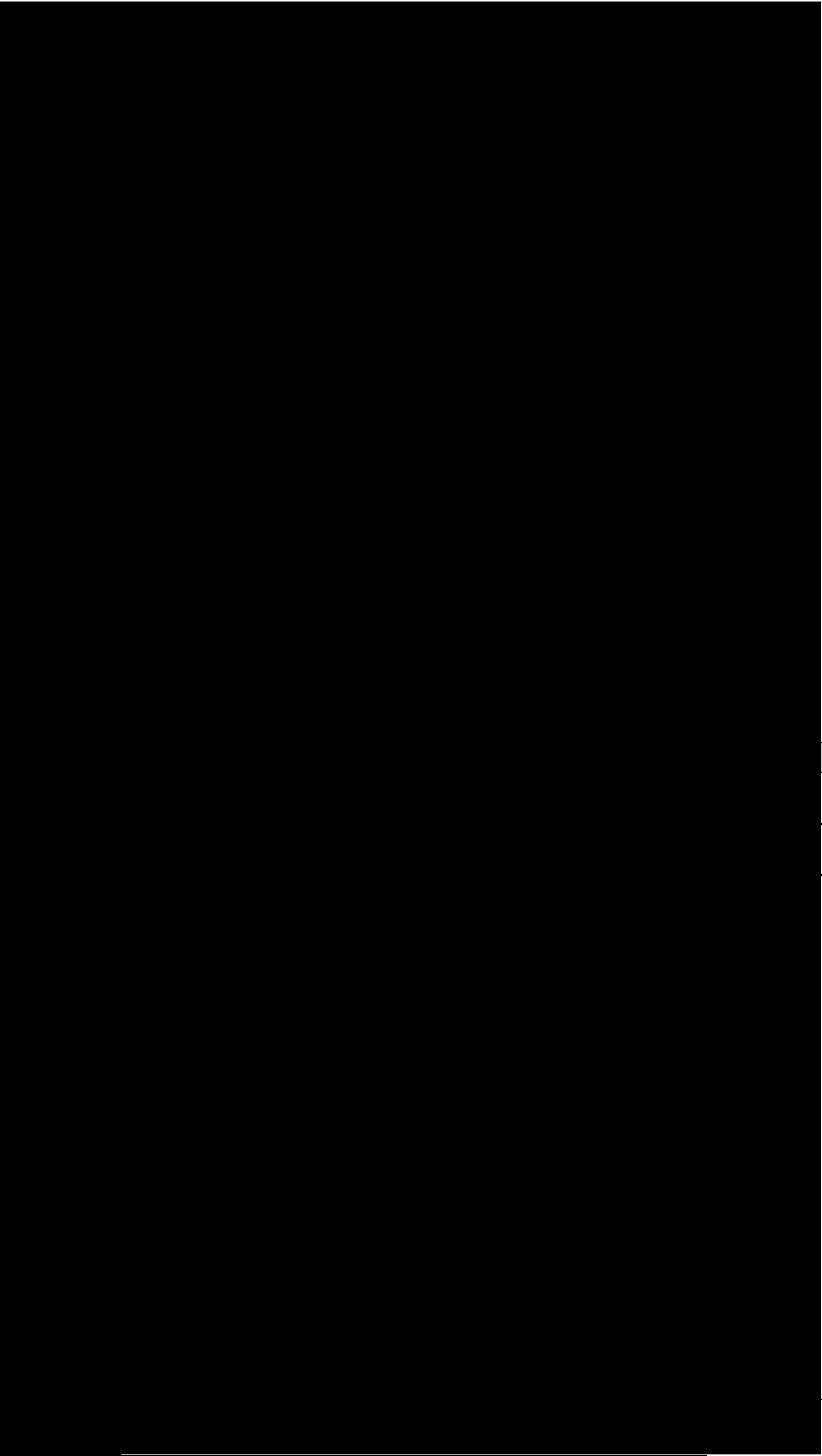






	°C					
	°C					
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FIG.1:Power dissipation vs. on-state current
(per thyristor or diode)

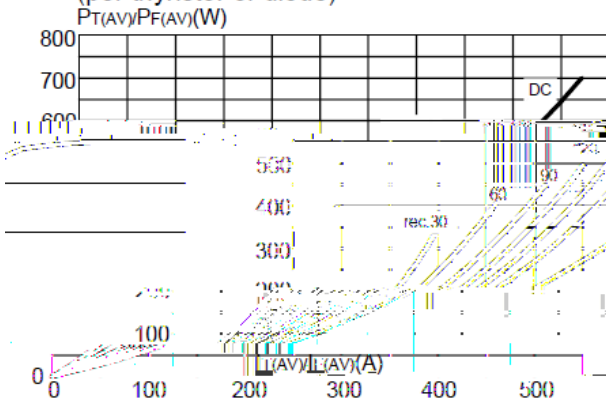


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

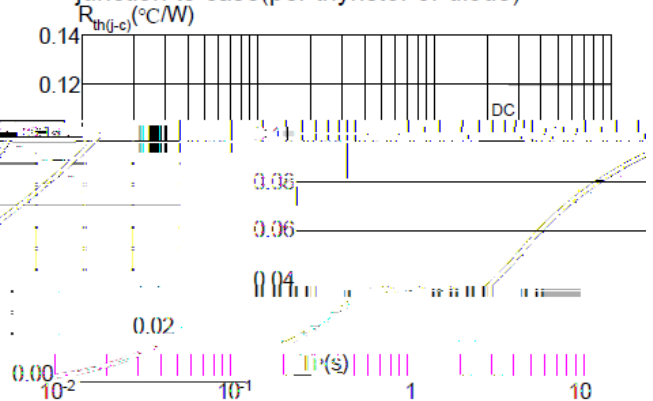


FIG.3:Forward characteristics
(per thyristor or diode)

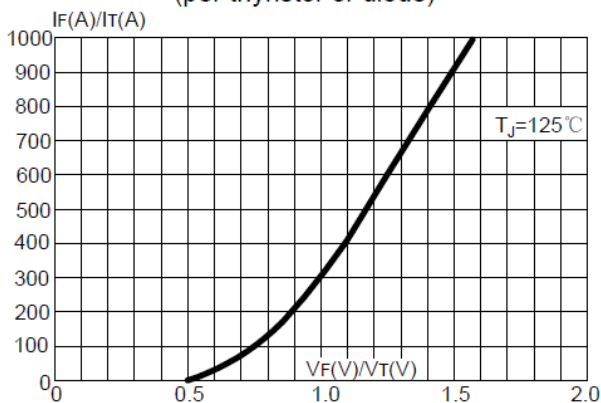


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

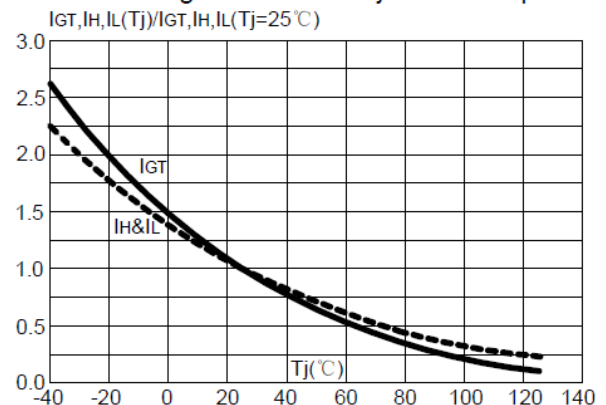


FIG.5:Gate trigger characteristics
(per thyristor or diode)

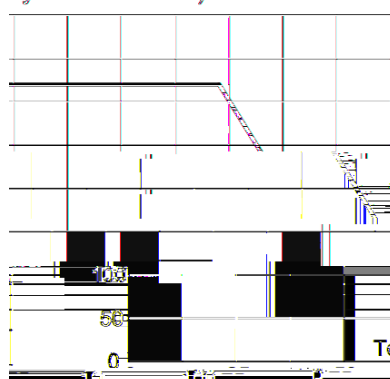


FIG.6: Forward current vs. case temperature

